

DDR3 SDRAM SO-DIMM (PC3-12800 4GB) FN12N004GL-M414CC0

Rev. 1.00

Features

- JEDEC Standard 204-pin Dual In-Line Memory Module
- Intend for PC3-12800 applications
- Inputs and Outputs are SSTL-15 compatible
- VDD=VDDQ= 1.35Volt(-0.067/+0.1V)or 1.5Volt
- Bi-directional Differential Data Strobe
- DLL aligns DQ and DQS transition with CK transition
- Normal and Dynamic On-Die Termination support
- Golden Connector
- 8 bit pre-fetch
- Two different termination values (Rtt_Nom & Rtt_WR)
- Auto & self refresh 7.8μs (TA ≤ +85°C)
- SDRAM operating temperature range
-20°C ≤ TA ≤ +85°C
- Programmable Device Operation:
 - Burst Type: Sequential or Interleave
 - Device CAS# Latency: 7,9,11
 - Burst Length: switch on-the-fly: BL=8 or BC 4
- RoHS Compliant

Part Number	FN12N004GL-M414CC0
Density	4GB
Module speed	PC3-12800 (DDR3-1600)
Function	Non ECC
Operating Temp	0 to +85°C
Organization	512Mx64
Component Composition	512Mx8 Micron*8
Number of Rank	1
Height	30mm
Golden Connector	Au:3u"
Chamfer	Yes

Key Parameter

Part Number	Module speed	tRCD (ns)	tRP (ns)	tRC (ns)	CL-tRCD-tRP
FN12N004GL-M414CC0	PC3-12800 (DDR3-1600)	13.125	13.125	48.125	11-11-11

Environmental Req.

Symbol	Parameter	Rating	Units	Notes
TOPR	Operating Temperature (ambient)	0 to +85	°C	1,2
		+85 to +95	°C	1,2
TSTG	Storage Temperature	-50 to +100	°C	-
HOPR	Operating Humidity (relative)	10 to 90	%	-
HSTG	Storage Humidity (without condensation)	5 to 95	%	-

1. The component maximum case temperature (Tcase) shall not exceed the value specified in the DDR DRAM component specification.
2. Average Refresh Period 7.8us at lower then TCASE 85°C, 3.9us at 85°C < TCASE ≤ 95°C

Absolute Max DC Rating

Symbol	Parameter	Rating	Units	Notes
V _{IN} , V _{OUT}	Voltage on any pins relative to V _{SS}	-0.4 to +1.8	V	1
V _{DD}	Voltage on V _{DD} supply relative to V _{SS}	-0.4 to +1.8	V	1,2
V _{DDQ}	Voltage on V _{DDQ} supply relative to V _{SS}	-0.4 to +1.8	V	1,2

- Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is stress rating only, and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- V_{DD} and V_{DDQ} must be within 300 mV of each other at all times; and V_{REF} must be not greater than 0.6 x V_{DDQ}, When V_{DD} and V_{DDQ} are less than 500 mV; V_{REF} may be equal to or less than 300 mV

Operating Conditions

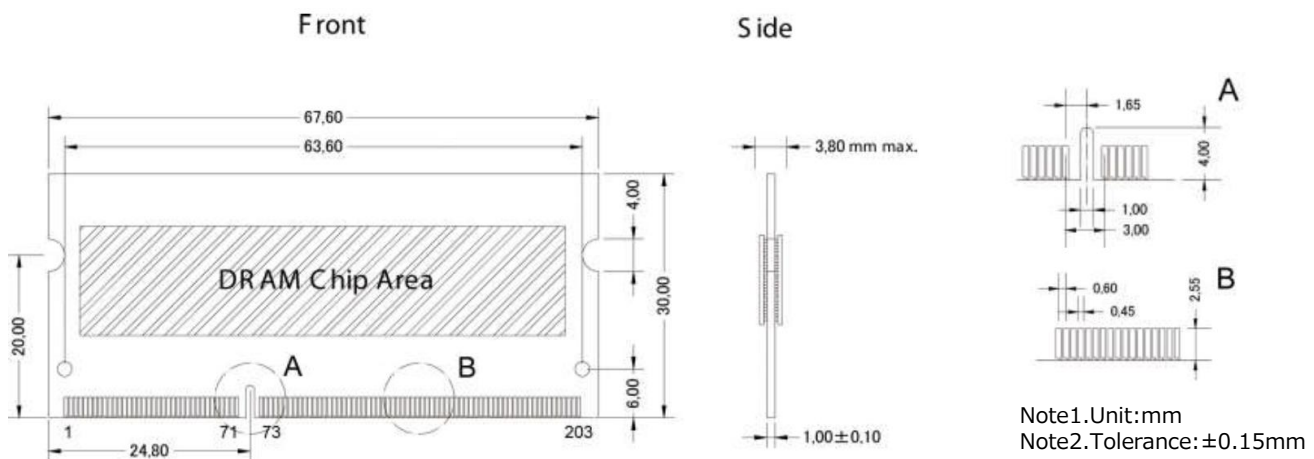
- Recommended DC Operating Conditions - DDR3L (1.35V) operation

Voltage referenced to V_{SS} = 0V, V_{DD}&V_{DDQ}=1.35 V +0.100/- 0.067V, T_c = 0 to 85°C

Symbol	Parameter	Min	MAX	Units	Notes
V _{DD}	Supply Voltage	1.283	1.45	V	1,2
V _{DDSPD}		3	3.6	V	
V _{DDQ}	Supply Voltage for Output	1.283	1.45	V	1,2
V _{REFCA} , (DC)	I/O Reference Voltage(CMD/ADD)	0.49 x V _{DDQ}	0.51 x V _{DDQ}	V	3,4
V _{REFDQ} , (DC)	I/O Reference Voltage(DQ)	0.49 x V _{DDQ}	0.51 x V _{DDQ}	V	3,4

- Under all conditions V_{DDQ} must be less than or equal to V_{DD}.
- V_{DDQ} tracks with V_{DD}. AC parameters are measured with V_{DD} and V_{DDQ} tied together.
- The AC peak noise on V_{REF} may not allow V_{REF} to deviate from V_{REF}(DC) by more than anent d (for reference: approx. ±13.5mV)
- For reference: approx. V_{DD}/2 ±13.5mV

Dimensions



HAGIWARA Solutions ハギワラ ソリューションズ 株式会社

本社 〒460-0003 愛知県名古屋市中区錦2-5-12 パシフィックスクエア名古屋 8F
8th floor, Pacific Square Nagoya Nishiki, 2-5-12 Nishiki, Nakaku, Nagoya City, Aichi 460-0003, Japan
Mail Address hsol.support@hagisol.co.jp

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